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Preliminary communication

Kinetic study on thermal syn-anti isomerization of dodecaisopropyltricyclo[4.2.0.0^{2,5}]octasilane¹

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Abstract

When heated at 493 K, syn-dodecaisopropyltricyclo[4.2.0.0^{2.5}]octasilane (syn-1) isomerizes to antidodecaisopropyltricyclo[4.2.0.0^{2.5}]octasilane (anti-1); isomerization of anti-1 to syn-1 does not occur at 493 K. Thermodynamic parameters were determined for the one-way isomerization of syn-1 to anti-1: $E_a = 42.3 \text{ kcal mol}^{-1}$, $\log A = 15.1 \text{ s}^{-1}$, $\Delta H^{\ddagger} = 41.4 \text{ kcal mol}^{-1}$, $\Delta S^{\ddagger} = 7.6 \times 10^{-3} \text{ kcal mol}^{-1} \text{ K}^{-1}$ and $\Delta G_{493 \text{ K}}^{\ddagger} = 37.6 \text{ kcal mol}^{-1}$. The activation energy is considerably larger than that for the analogous thermal isomerization of syn-tricyclo[4.2.0.0^{2.5}]octane (syn-2) to anti-tricyclo[4.2.0.0^{2.5}]octane (anti-2), indicating that the bond dissociation energy of the bridgehead Si–Si bond of syn-1 is larger than that of the bridgehead C–C bond of syn-2.

Keywords: Silicon; Ladder polysilane; Thermolysis; syn-anti Isomerization; Kinetics

1. Introduction

Since the first ladder polysilane, decaisopropylbicyclo[2.2.0]hexasilane, was reported in 1987, the structures, electronic properties and reactions of ladder polysilanes have been investigated by our group [1]. The ladder polysilanes were prepared via the co-condensation of 1,2-dichloro-1,1,2,2-tetraisopropyldisilane and 1,1,2,2-tetrachloro-1,2-diisopropyldisilane with lithium, and we found that the reaction afforded both anti-dodecaisopropyltricyclo[4.2.0.0^{2.5}]octasilane (anti-1) and syn-dodecaiscpropyltricyclo[4.2.0.0^{2.5}]octasilane (syn-1) [2]. X-ray crystallographic studies showed that: syn-1 has a more strained structure than anti-1; the Si-Si bond lengths in syn-1 (2.369(4)-2.436(4) Å, average 2.402 Å) are longer than those in anti-1 (2.346(3)--2.405(4) Å, average 2.388 Å) [2]. This prompted us to examine the thermal stability of these isomers. We report below the results of a study on the thermal isomerization of syn-1 to anti-1, and discuss the thermodynamic parameters for the isomerization.

2. Results and discussion

When a solution of syn-1 in decahydronaphthalene was heated at 493 K, syn-1 isomerized to anti-1 quantitatively. When anti-1 in decahydronaphthalene was likewise heated at 493 K, no isomerization of anti-1 to syn-1 was observed, and anti-1 was recovered. It is noteworthy that the thermolysis of syntricyclo[4.2.0.0^{2,5}]octane (syn-2) was reported to give 1,5-cyclooctadienes, anti-tricyclo[4.2.0.0^{2,5}]octane (anti-2) and 1,2-divinylcyclobutanes in 51%, 41% and 8% respectively [3]. The results indicate that there is a significant difference in the thermolysis pathway for syn-1 and syn-2.



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It is interesting to compare thermodynamic parameters for the isomerization process from syn-1 to anti-1

¹ Dedicated to Professor Robert Corriu in recognition of his outstanding contributions to organosilicon chemistry.



Fig. 1. Plot of $\ln(1 + [anti-1]/[syn-1])$ vs. t for thermal isomerization of syn-1 to anti-1.

with those reported for the isomerization of syn-2 to *anti-2* [3]. To allow such a comparison, a kinetic study was carried out. The thermal isomerization of syn-1 to *anti-1* shows a first-order dependence on the concentration of syn-1 in accord with Eq. (1).

$$\ln(1 + [anti-1]/[syn-1]) = kt$$
(1)

Fig. 1 shows the plot of $\ln(1 + [anti-1]/[syn-1])$ vs. t. Each plot shows good linearity with a correlation coefficient of 0.999. The rate constants are listed in Table 1. In Fig. 2 are shown plots of $\ln k$ vs. T^{-1}

 Table 1

 Thermodynamic parameters for thermal isomerization of syn-1 to anti-1

(r = -0.9996) and $\ln k/T$ vs. T^{-1} (r = -0.9996); from these, the thermodynamic parameters were determined by use of the following equations, where *R*, **k** and *h* are the gas constant, the Boltzmann constant and the Planck constant respectively. These parameters are listed in Table 1.

$$\ln k = -E_a/RT + \ln A \tag{2}$$

$$\ln k/T = -\Delta H^{\ddagger}/RT + \Delta S^{\ddagger}/R + \ln k/h$$
(3)

$$\Delta G^{\ddagger} = RT(\ln k T/h - \ln k) \tag{4}$$

In the thermal isomerization of syn-1 to anti-1, a relatively high temperature (473-493 K) is necessary because of the large activation energy $(42.3 \text{ kcal mol}^{-1})$. Since the heat of formation of syn-1 calculated by the MM2 method is larger than that of anti-1 by 13.4 kcal mol⁻¹, the activation energy for the isomerization of anti-1 to syn-1 is estimated to be greater than 55 kcal mol⁻¹, so that isomerization of anti-1 to syn-1 cannot take place at 493 K. In contrast, it has been reported that the activation energy for thermal isomerization of syn-2 to anti-2 is relatively low $(31.4 \text{ kcal mol}^{-1})$, and that isomerization occurs at lower temperatures (390-419K) [3]. At present, the mechanism of the thermal isomerization of syn-1 to anti-1 is not clear. However, if it is assumed to proceed via a biradical intermediate, as reported for the isomerization

T (K)	k (s ⁻¹)	ΔG^{\dagger} (kcal mol ⁻¹)	E_a (kcal mol ⁻¹)	$\log A(s^{-1})$	ΔH^{1} (kcal mol ⁻¹)	ΔS^{1} (kcal mol ⁻¹ K ⁻¹)
			42.3 ± 0.4	15.1 ± 0.2	41.4 ± 0.4	$(7.6 \pm 0.8) \times 10^{-3}$
493	(2.17 ± 0.09) × 10 ⁻⁴	37.63 ± 0.04				
488	$(1.44 \pm 0.06) \times 10^{-4}$	37.63 ± 0.04				
483	$(9.32 \pm 0.38) \times 10^{-5}$	37.66 ± 0.04				
478	$(5.68 \pm 0.18) \times 10^{-5}$	37.73 ± 0.03				
473	$(3.53 \pm 0.09) \times 10^{-5}$	37.77 ± 0.02				



Fig. 2. Plots of ln k vs. T^{-1} (k.t) and ln k/T vs. T^{-1} (right) for thermal isomerization of syn-1 to anti-1.

of syn-2 [3], the activation energy approximately corresponds to the bond dissociation energy. Although the bond dissociation energy of the bridgehead Si-Si bond of syn-1 is much smaller than those of common Si-Si bonds (ca. 70–80 kcal mol⁻¹) [4] because of ring strain, it is significantly larger than that of the bridgehead C-C bond of syn-2. The larger bond dissociation energy of the bridgehead Si-Si bond of syn-1 may be attributed in part to the reduced ring strain in ladder polysilanes compared with that in ladderanes [5]. The log A value for the thermal isomerization of syn-1 to anti-1 (15.1 s^{-1}) is slightly larger than that for the thermal isomerization of syn-2 to anti-2 (13.4 s^{-1}) . The activation entropy $(7.6 \times 10^{-3} \text{ kcal mol}^{-1} \text{ K}^{-1})$ is very low, in accord with the fact that the thermal isomerization is a unimolecular reaction.

3. Experimental

syn-Dodecaisopropyltricyclo[$4.2.0.0^{2.5}$]octasilane (syn-1) was prepared as previously described [2]. Decahydronaphthalene was treated with concentrated sulfuric acid, washed successively with aqueous sodium hydrogen carbonate and aqueous sodium chloride, dried over calcium chloride and distilled from sodium wire. Thermal reactions were carried out in a silicone oil bath (Toray Dow-Corning Silicone, SRX310), the temperature of which was controlled to within ± 0.1 K, using a Riko MSR-15D magnetic stirrer. HPLC analyses were performed with an ODS column (Chemco, chemcosorb 5-ODS-H, 4.6×250 mm) using methanol-THF (7:3) as an eluent.

3.1. Kinetic measurement of thermal isomerization of syn-1 to anti-1

A solution of *syn*-1 in decahydronaphthalene (0.07 M) was degassed by freeze-pump-thaw cycles and the glass tube containing the solution was sealed and placed in a silicone oil bath at 473–493 K. After an appropriate

time, the tube was opened, and the concentration ratio of *anti*-1 to *syn*-1 was determined by HPLC.

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